

**FERROELECTRIC MEMORY DEVICES HAVING AN EXPANDED PLATE ELECTRODE AND METHODS FOR FABRICATING THE SAME**

**ABSTRACT OF THE DISCLOSURE**

5       Ferroelectric memory devices are formed on an integrated circuit substrate. A bottom interlayer dielectric layer is positioned on the integrated circuit substrate and a plurality of ferroelectric capacitors are arranged in a row and column relationship on the bottom interlayer dielectric layer. A top interlayer dielectric layer is disposed on a surface of the integrated circuit substrate including the plurality of ferroelectric  
10      capacitors. The top interlayer dielectric layer includes via holes disposed on and associated with ones of the ferroelectric capacitors. A plate electrode is formed in the top interlayer dielectric layer. The plate electrode extends into respective ones of the via holes to contact top surfaces of at least two neighboring ones of the plurality of ferroelectric capacitors. Methods or fabricating ferroelectric memory devices are also  
15      provided

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